

## ABSTRACT OF THE DISCLOSURE

A method of forming a metal wiring in a semiconductor device is disclosed. In order to improve a low deposition speed in the process technology by which a damascene pattern of an ultra-fine structure is filled with copper by CVD method, a  
5 CECVD method is disclosed by which a chemical enhancer layer for increasing the deposition speed of copper is formed and the damascene pattern is then filled by means of MOCVD method using a copper precursor which forms a copper wiring. A diffusion prevention film is formed on the sidewall of the damascene pattern in the  
10 shape of a spacer in order to prevent an increase of the via resistance by the diffusion of copper into the sidewalls of the damascene pattern. A chemical enhancer layer is selectively formed on a lower metal layer that is exposed by the damascene pattern, thus allowing a selective partial filling of the damascene pattern. Therefore, copper  
filling in an ultra-fine structure is facilitated which also minimizes the electrical resistivity of the copper wiring.

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